

• General Description

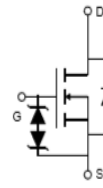
The ZMD68203U combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Dual DIE in one package

• Application

- Power Management in Notebook Computer,
- Portable Equipment and Battery Powered Systems

• Product Summary


$V_{DS1} = 20V$
 $V_{DS2} = 20V$
 $R_{DS(ON)1} = 13m\Omega$
 $R_{DS(ON)2} = 13m\Omega$
 $I_{D1} = 6.5A$
 $I_{D2} = 6.5A$

G1 D1/D2 G2



S1 D1/D2 S2



SOT23-6

• Ordering Information:

Part NO.	ZMD68203U
Marking	ZMD68203
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

• Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	6.5	A
	$I_{D@TC=75^\circ C}$	4.9	A
	$I_{D@TC=100^\circ C}$	4.1	A
Pulsed Drain Current ^①	I_{DM}	15	A
Total Power Dissipation($TC=25^\circ C$)	$P_D@TC=25^\circ C$	3.6	W
Total Power Dissipation($TA=25^\circ C$)	$P_D@TA=25^\circ C$	0.69	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	30	mJ

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	2.5	$^{\circ}C/W$
Thermal resistance, junction - ambient	R_{thJA}	-	-	70	$^{\circ}C/W$
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	$^{\circ}C$

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	0.5		1.2	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 6.5A$		13	15	m Ω
		$V_{GS} = 2.5V, I_D = 5A$		18	20	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 20V, I_D = 5A$		9		S
Source-drain voltage	V_{SD}	$I_S = 6.5A$			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$f = 1MHz$	-	650	-	pF
Output capacitance	C_{oss}		-	190	-	
Reverse transfer capacitance	C_{rss}		-	115	-	

•Gate Charge characteristics($T_a = 25^{\circ}C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 15V$	-	11	-	nC
Gate - Source charge	Q_{gs}	$I_D = 3A$	-	5	-	
Gate - Drain charge	Q_{gd}	$V_{GS} = 4.5V$	-	4	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Fig.1 Power Dissipation

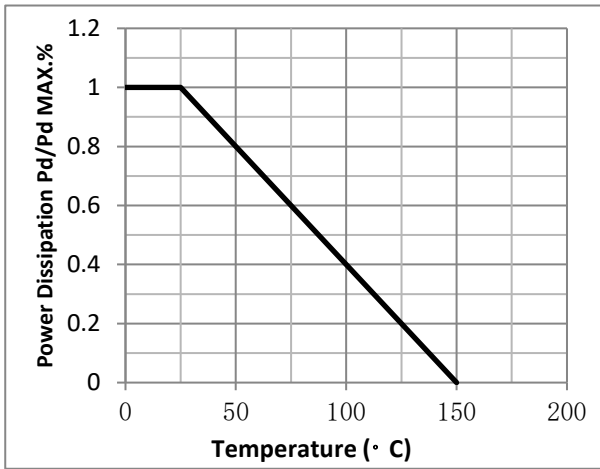


Fig.2 Typical output Characteristics

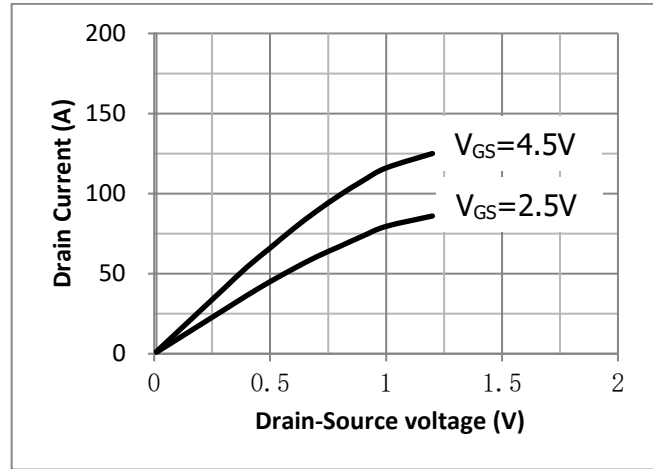


Fig.3 Threshold Voltage V.S Junction Temperature

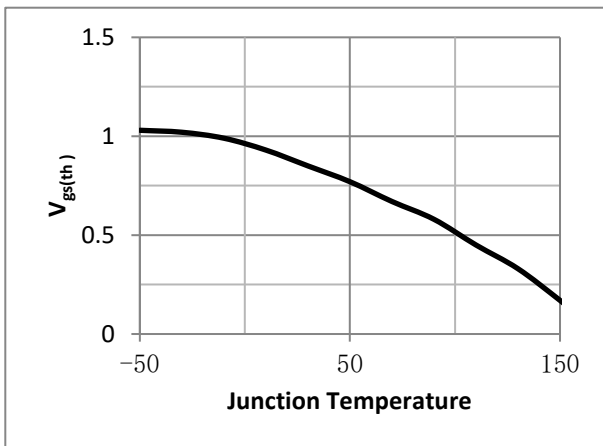


Fig.4 Resistance V.S Drain Current

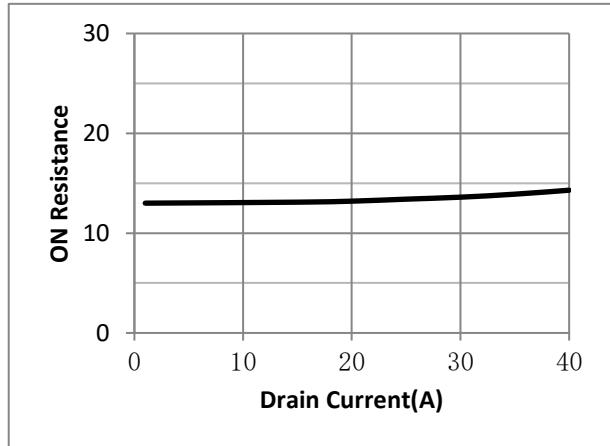


Fig.5 On-Resistance VS Gate Source Voltage

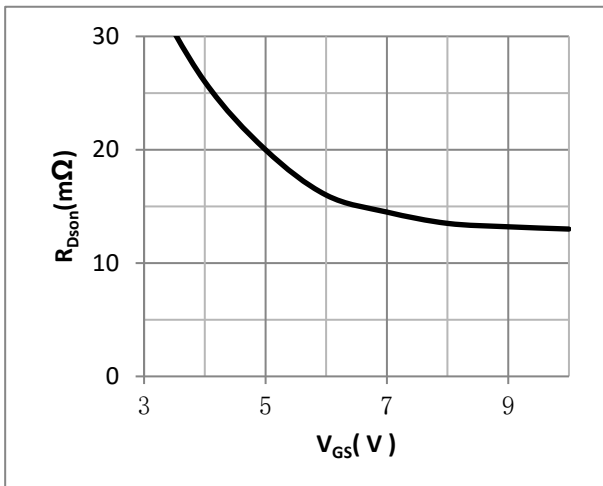


Fig.6 On-Resistance V.S Junction Temperature

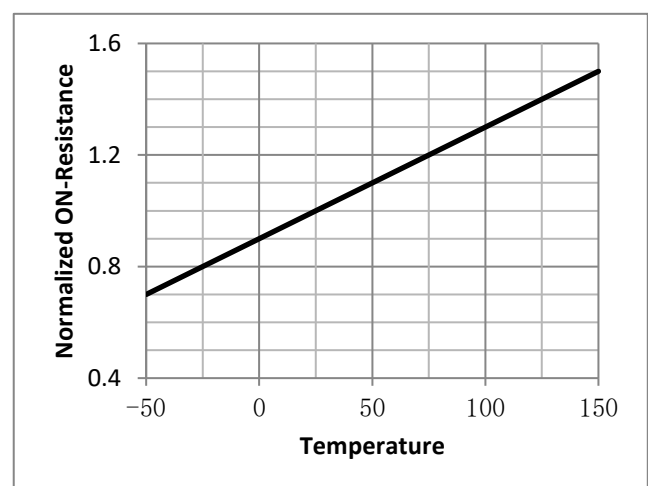


Fig.7 Switching Time Measurement Circuit

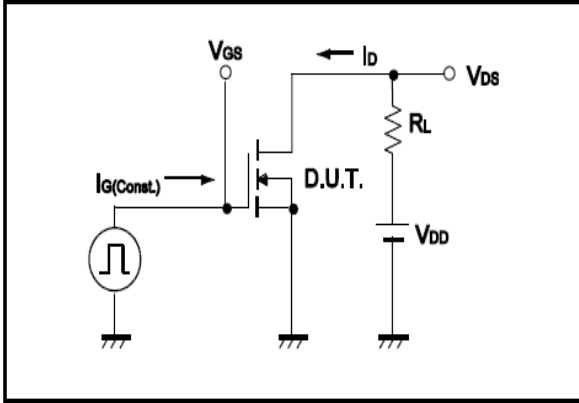


Fig.8 Gate Charge Waveform

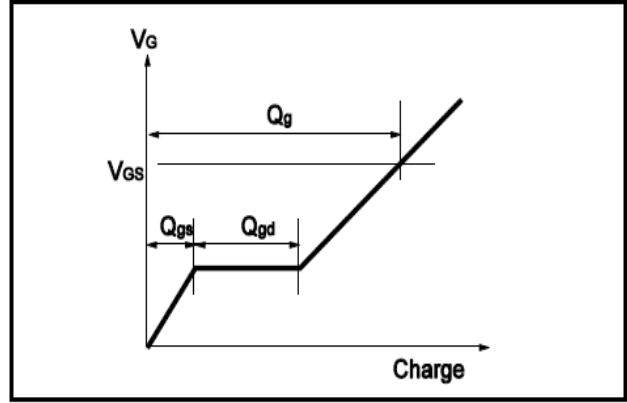


Fig.9 Switching Time Measurement Circuit

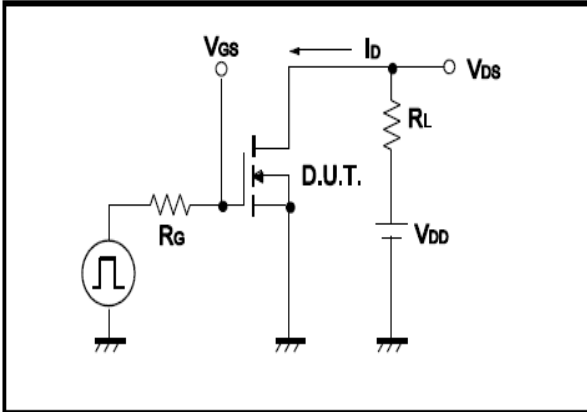


Fig.10 Gate Charge Waveform

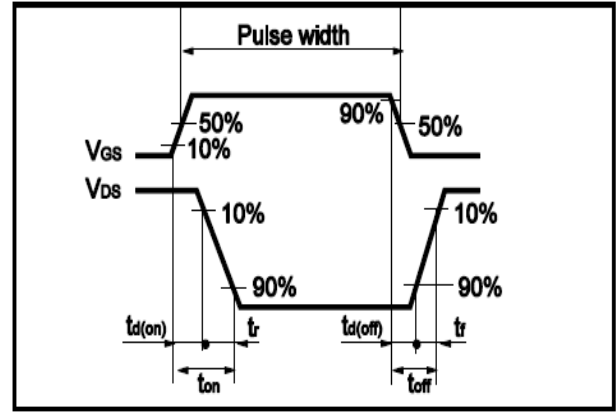


Fig.11 Avalanche Measurement Circuit

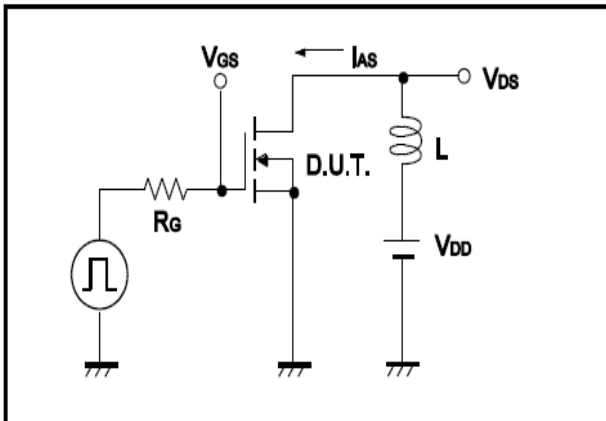
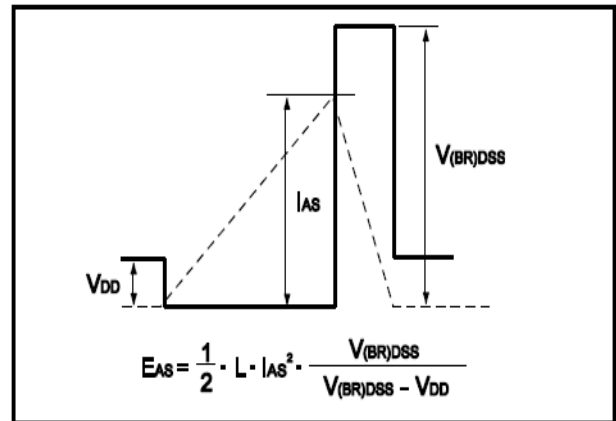


Fig.12 Avalanche Waveform



•Dimensions(SOT23-6)

Unit: mm

